



Fine-tuning the etch depth profile via dynamic shielding of ion beam



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ABSTRACT

We introduce a method for finely adjusting the etch depth profile by dynamic shielding in the course of ion beam etching (IBE), which is crucial for the ultra-precision fabrication of large optics. We study the physical process of dynamic shielding and propose a parametric modeling method to quantitatively analyze the shielding effect on etch depths, or rather the shielding rate, where a piecewise Gaussian model is adopted to fit the shielding rate profile. Two experiments were conducted. The experimental result of parametric modeling of shielding rate profiles shows that the shielding rate profile is significantly influenced by the rotary angle of the leaf. The result of the experiment on fine-tuning the etch depth profile shows good agreement with the simulated result, which preliminarily verifies the feasibility of our method.

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1. Introduction

As a state-of-the-art technique, IBE plays a crucial role in the ultra-precision fabrication of large optics such as X-ray mirrors [1–3], vacuum ultraviolet gratings [4,5], and beam sampling gratings (BSGs) [6,7]. Collimators or shutters are usually used to adjust the etch rate profile [3,8] in order to meet the desired etch depth map. Peverini et al. presented an IBE technique using a double-blade system to profile flat optics into aspherical X-ray mirrors [3]. In the fabrication of BSGs, we also encountered a similar scenario and needed to adjust the spatial distribution of etch depths. Compared to surfacing of X-ray mirrors, fine-tuning of etch depths in the course of IBE of BSGs is, to some extent, more difficult and requires more flexibility [6,7,9]. On one hand, the etch depths are almost randomly distributed. On the other, the adjustment of etch depths is quite fine and slight compared with the maximum etch depth. Hence, in our previous work [7,9], we proposed a new solution for fabricating the large-aperture BSG of high diffraction uniformity as well as algorithms for finely tuning the spatial distribution of etch depths.

To put the idea into practice, we investigate the physical process of dynamic shielding and introduce how to calculate the shielding time. With a graphite leaf, the ion beam emitted from a linear ion source is locally blocked. The leaf scans along the major axis of the ion source and simultaneously rotates about itself, then

the ion beam impinging on the substrate to be etched is dynamically adjusted. Also, we conduct quantitative analysis on the shielding effect on etch depths, or rather the shielding rate. A piecewise Gaussian model is adopted to fit the shielding rate profile. Finally, experiments are conducted for parametric modeling of the shielding rate profile and verifying the feasibility of fine-tuning the etch depth profile.

2. Dynamic shielding during ion beam etching

2.1. Shielding rate profile

A dynamic leaf, which is a rectangular thin graphite plate, was designed and it is dragged by stepper motors. As illustrated in Fig. 1, the dynamic leaf has two degrees of freedom, i.e., scanning vertically and swinging about itself within a limited angular range. During the etch process, the dynamic leaf locally blocks the ion beam and then a shadow is formed on the substrate. To quantitatively describe the shadow, the shielding rate profile is introduced (see Fig. 1), where the shielding rate reflects the shielding effect on protecting the materials from etching. The shielding rate of 0 indicates no shielding and that of 1 indicates full shielding and being free of etching.

The full-width-half-maximum (FWHM) of the shielding rate profile is defined as the shadow width, which is different from the projected width of the dynamic leaf. As is shown in Fig. 1, the projected width can be calculated as

$$W_{proj} = W_{leaf} \sin \theta + H_{leaf} \cos \theta, \quad (1)$$

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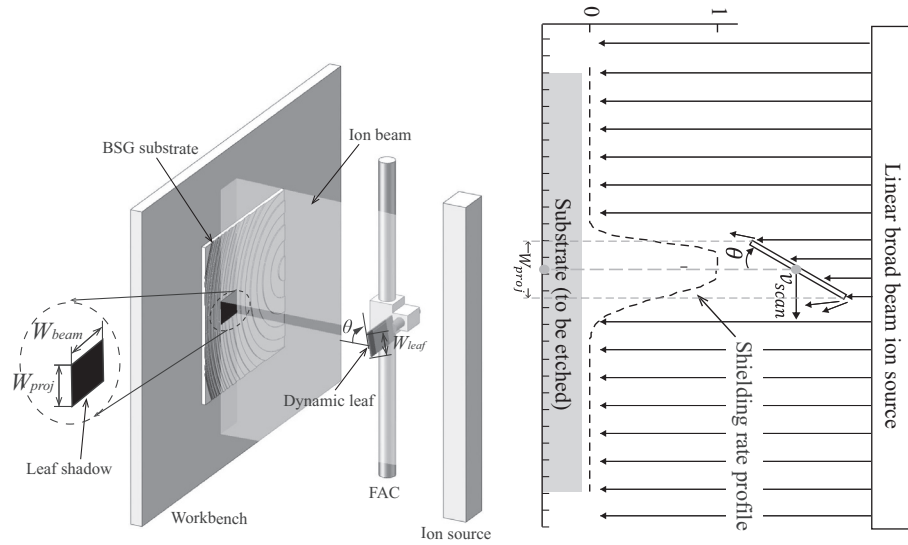


Fig. 1. Dynamic shielding during IBE. The left illustrates the IBE of BSG and the right is the abstract model in 2D. Where W_{proj} is the projected width, W_{beam} is the beam width, W_{leaf} is the leaf width, θ is the rotary angle of the dynamic leaf, and v_{scan} is the constant scanning velocity.

where W_{proj} is the projected width, W_{leaf} is the leaf width, H_{leaf} is the leaf thickness, and θ is the rotary angle of the dynamic leaf. Note that, in this paper, we focus on the 1D analysis of the leaf shadow and the shielding rate profile, so it is assumed that the beam width W_{beam} , as illustrated in Fig. 1, has nothing to do with the shielding rate.

A piecewise Gaussian model is applied to fitting the shielding rate profile, which is given by

$$PWG(x; a, b, c_1, c_2) = \begin{cases} ae^{-\left(\frac{x+b}{c_1}\right)^2} & \text{for } x < -\frac{b}{2} \\ ae^{-\left(\frac{x-b}{c_2}\right)^2} & \text{for } x > \frac{b}{2} \\ a & \text{otherwise} \end{cases}, \quad (2)$$

The FWHM of the piecewise Gaussian is defined as

$$FWHM\{PWG(x; a, b, c_1, c_2)\} = b + \sqrt{\ln 2}(c_1 + c_2), \quad (3)$$

where $\sqrt{\ln 2}c_1$ and $\sqrt{\ln 2}c_2$ are the FWHMs of the left half-Gaussian and the right half-Gaussian.

2.2. Calculation of the shielding time

The shielding time of a point herein refers to the total elapsed time the point is shielded by the dynamic leaf. For clarity, the term, dwell time used in the previous paper [7], is renamed as shielding time hereafter. To calculate the shielding time, we should map the shielding rate profiles onto the spatial temporal coordinate system and then, as shown in Fig. 2, integrate the fitted shielding rate profile over time. The plots at the top of Fig. 2 show the rotary angle profile and the corresponding projected width profile, which, accompany with the constant scanning velocity, determines the motion trajectory of the dynamic leaf, i.e., scanning at a constant speed and swinging between 0° and 90° simultaneously. The left part of Fig. 2 presents the calculated shielding time profiles, of which the solid curve is the actual shielding time profile and the symmetric dashed curve indicates the approximate result assuming that full shielding occurs in the projected area and there are free of shielding in other areas. Obviously, the actual shielding time profile is asymmetric due to the asymmetry of the shielding rate profile, which will be discussed in the following section.

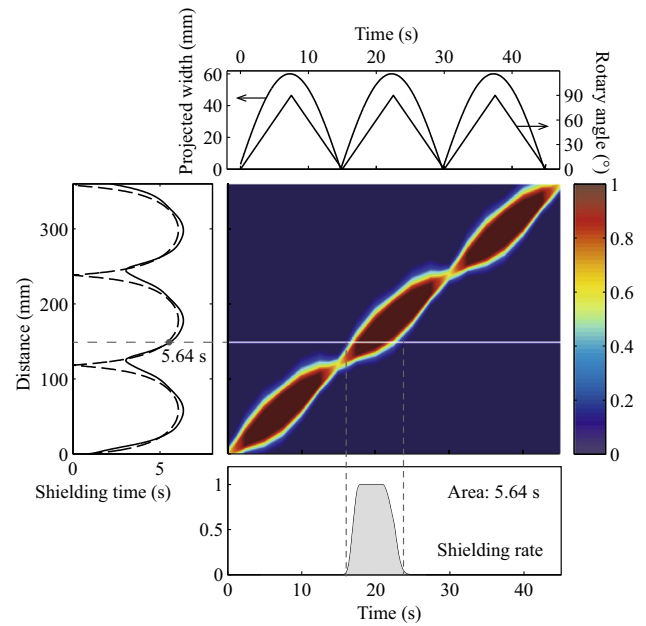


Fig. 2. Calculation of shielding time. The plots at the top show the rotary angle profile and the corresponding projected width profile. The lower plot shows the shielding rate profile at the distance of 150 mm and the calculated shielding time is 5.64 s. The left part presents two shielding time profiles, of which the solid curve represents the actual result and the dashed curve represents the approximate result. Note that the color bar indicates the shielding rate.

3. Results and discussions

3.1. Parametric modeling of shielding rate profiles

It has been observed that the shielding rate profile is influenced by the rotary angle of the dynamic leaf. To further quantify its influence on the distribution of etch depths, we have conducted a well-designed experiment, which consists of 5 groups in correspondence with rotary angles of 0° , 15° , 30° , 60° , and 90° , respectively. A number of pieces of fused quartz samples are prepared for the etching experiment and the etch depth is measured by a stylus profiler (AMBIOS XP-1) with vertical resolution of the order of 0.1 nm. In Fig. 3, the upper half shows the measured etch

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